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## NTE249 (NPN) & NTE250 (PNP) Silicon Complementary Transistors Darlington Power Amplifier

### Description:

The NTE249 (NPN) and NTE250 (PNP) are silicon complementary Darlington transistors in a TO3 type case designed for use as output devices in complementary general purpose amplifier applications.

### Features:

- High DC Current Gain:  $h_{FE} = 3500$  Typ @  $I_C = 10A$
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors

### Absolute Maximum Ratings:

Collector-Emitter Voltage, $V_{CEO}$ .....	100V
Collector-Base Voltage, $V_{CB}$ .....	100V
Emitter-Base Voltage, $V_{EB}$ .....	5V
Collector Current, $I_C$ .....	16A
Base Current, $I_B$ .....	500mA
Total Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	150W
Derate Above $25^\circ C$ .....	0.857W/ $^\circ C$
Operating Junction Temperature Range, $T_J$ .....	$-55^\circ$ to $+200^\circ C$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+200^\circ C$
Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	1.17 $^\circ C/W$

### Electrical Characteristics: ( $T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100mA, I_B = 0$ , Note 1	100	—	—	V
Collector-Emitter Leakage Current	$I_{CEO}$	$V_{CE} = 50V, I_E = 0$	—	—	3.0	mA
	$I_{CER}$	$V_{CB} = 100V, R_{BE} = 1k\Omega$	—	—	1.0	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{CB} = 100V, R_{BE} = 1k\Omega, T_A = +150^\circ C$	—	—	5.0	mA
		$V_{BE} = 5V, I_C = 0$	—	—	5.0	mA

Note 1. Pulse Test: Pulse Width = 300 $\mu s$ , Duty Cycle = 2%

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>ON Characteristics (Note 1)</b>						
DC Current Gain	$h_{FE}$	$V_{CE} = 3\text{V}$ , $I_C = 10\text{A}$	1000	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 10\text{A}$ , $I_B = 40\text{mA}$	—	—	2.5	V
		$I_C = 16\text{A}$ , $I_B = 80\text{mA}$	—	—	4.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 3\text{V}$ , $I_C = 10\text{A}$	—	—	3.0	V

Note 1. Pulse Test: Pulse Width = 300μs, Duty Cycle = 2%

